



40V/320A N-Channel Power MOSFET

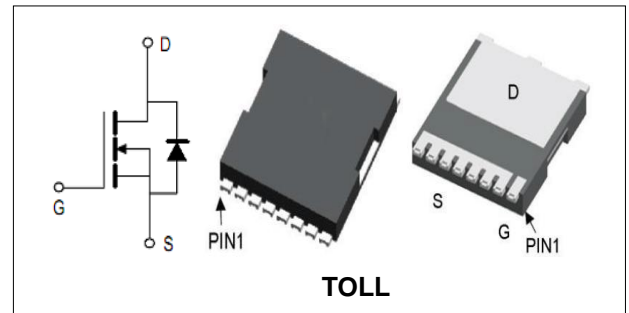
Features

- New technology for high voltage device.
- Low on-resistance and low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested

BVDSS	40	V
ID	320	A
RDSON@VGS=10V	0.62	mΩ

Applications

- DC/DC Converter
- Motor control and drives
- Battery management



Order Information

Product	Package	Marking	Reel Size	Reel	Carton
PGT04N010H	TOLL	PGT04N010H	13inch	1500PCS	12000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	TC =25°C 320	A
Mounted on Large Heat Sink			
E_{AS}	Single Pulse Avalanche Energy (Note1)	564	mJ
I_{DM}	Pulse Drain Current Tested (Silicon Limit) (Note2)	TC =25°C 1200	A
I_D	Continuous Drain current	TC =25°C 320	A
P_D	Maximum Power Dissipation	TC =25°C 300	W
$R_{θJc}$	Thermal Resistance Junction-to-Case (Note3)	0.42	°C/W

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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
I _{DSS}	Zero Gate Voltage Drain current	VDS=40V,VGS=0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	VDS=VGS,ID=250μA	2	2.3	3	V
R _{DS(ON)}	Drain-Source On-State Resistance (Note4)	VGS=10V, ID=75A	--	0.62	0.9	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note5)						
C _{iss}	Input Capacitance	VDS=25V,	--	9520	--	pF
C _{oss}	Output Capacitance	VGS=0V,	--	2060	--	pF
C _{rss}	Reverse Transfer Capacitance	F=300kHz	--	82	--	pF
Q _g	Total Gate Charge	VDS=20V,	--	159	--	nC
Q _{gs}	Gate-Source Charge	ID=50A,	--	51	--	nC
Q _{gd}	Gate-Drain Charge	VGS=10V	--	37	--	nC
Switching Characteristics (Note5)						
t _{d(on)}	Turn-on Delay Time	VDS=20V,	--	24	--	nS
t _r	Turn-on Rise Time	ID=50A	--	13	--	nS
t _{d(off)}	Turn-off Delay Time	RG=1.6Ω,	--	94	--	nS
t _f	Turn-off Fall Time	VGS=10V	--	16	--	nS
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	ISD=75A,VGS=0V	--	--	1.2	V

Note:

- Limited by T_{Jmax}, starting T_J = 25° C, R_G = 25Ω, V_D =30V, VGS =10V. Part not recommended for use above this value.
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.



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Typical Characteristics

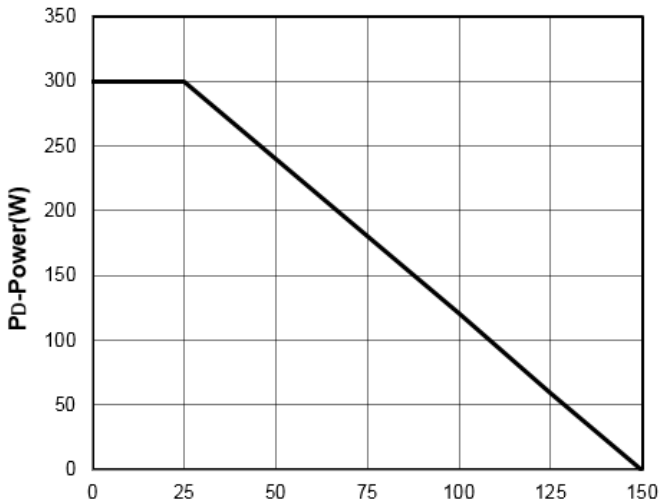


Figure1: T_J- Junction Temperature (°C)

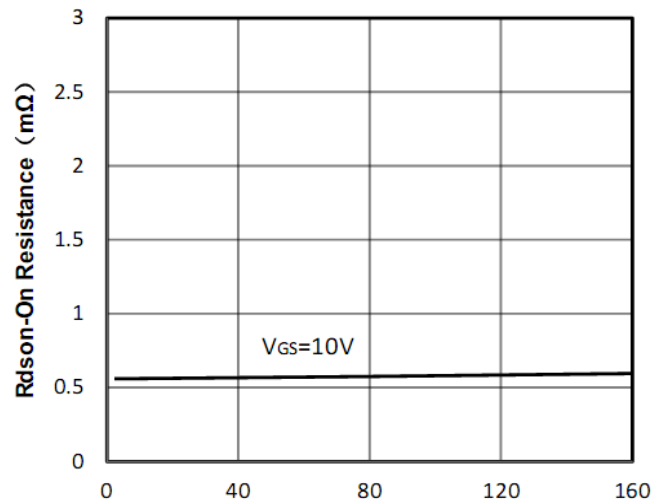


Figure2: I_D- Drain Current (A)

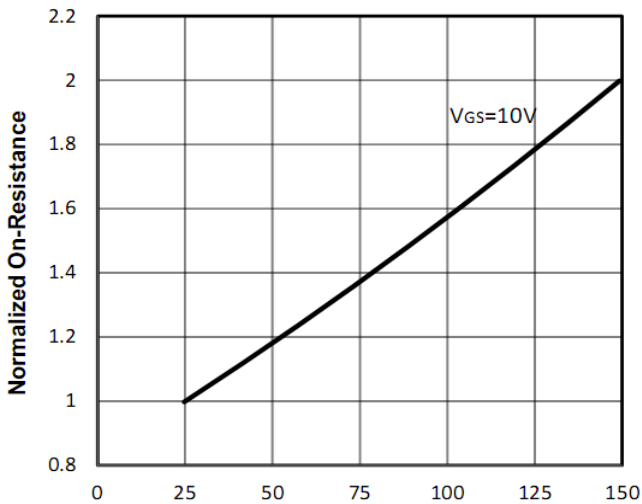


Figure3: T_J- Junction Temperature (°C)

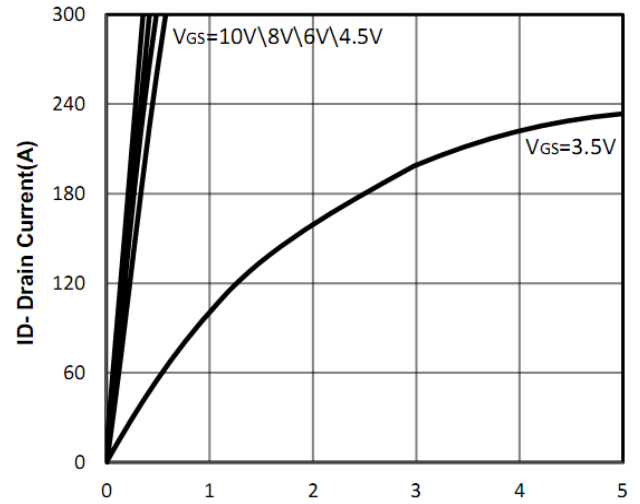


Figure4: V_{DS}- Drain-Source Voltage (V)

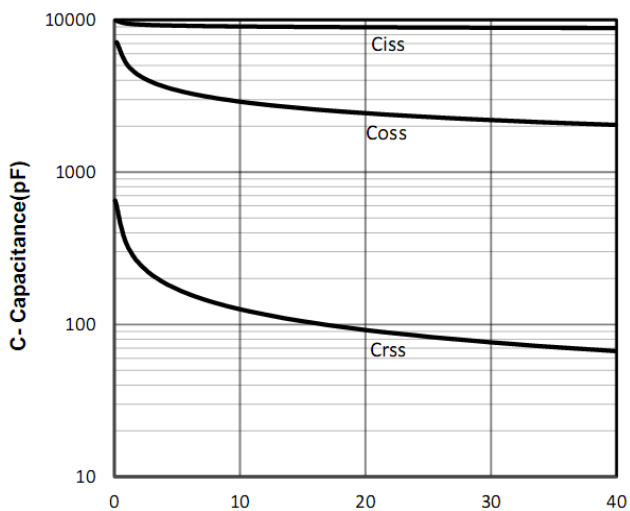


Figure5: V_{DS}- Drain-Source Voltage (V)

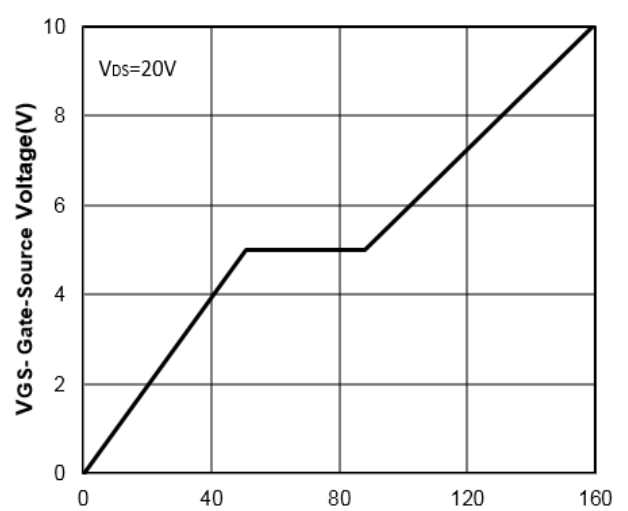


Figure6: Q_g- Gate Charge (nC)



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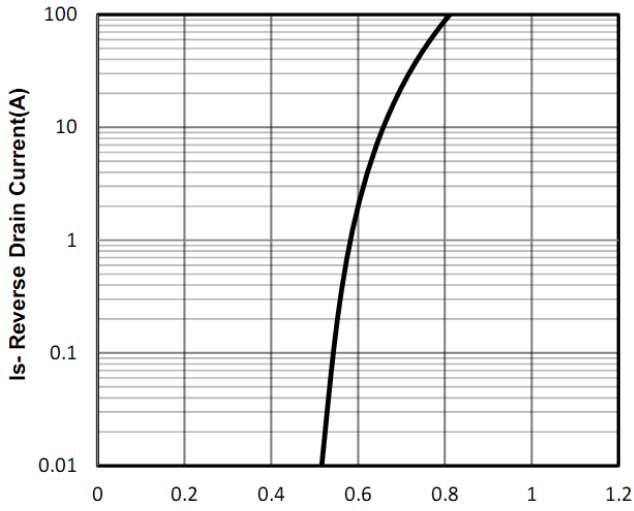


Figure7: Vsd- Source-Drain Voltage (V)

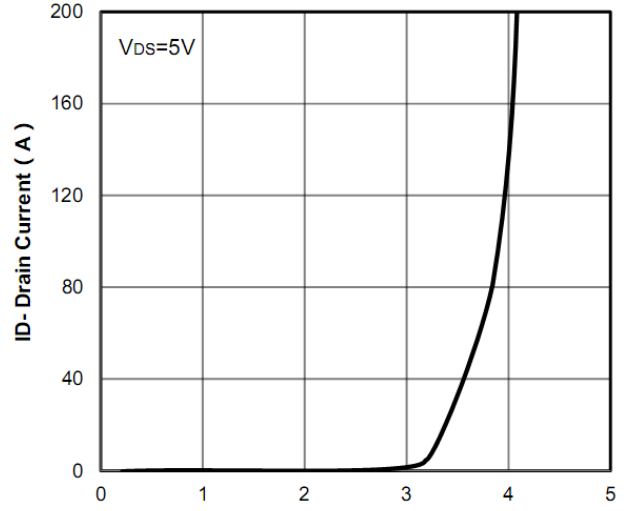


Figure8: Vgs- Gate-Source Voltage (V)

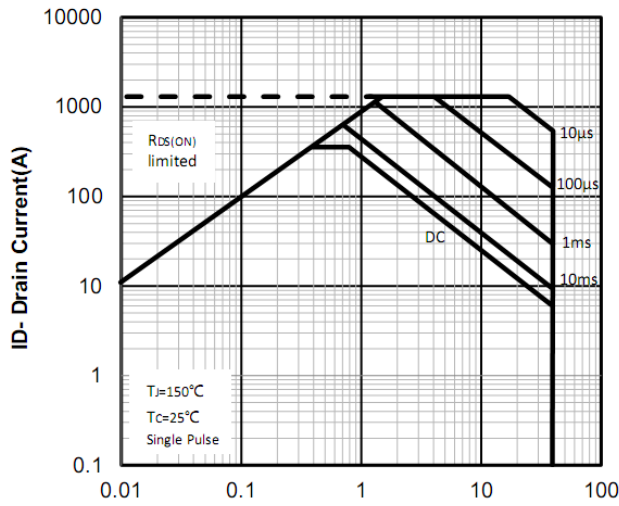


Figure9: Vds- Drain -Source Voltage (V)

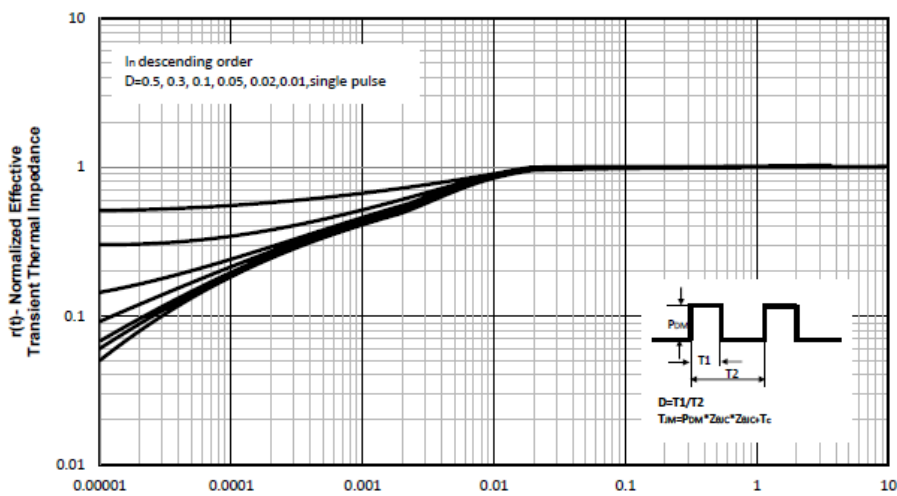


Figure10: Square Wave Pulse Duration (sec)

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Test Circuit and Waveform:

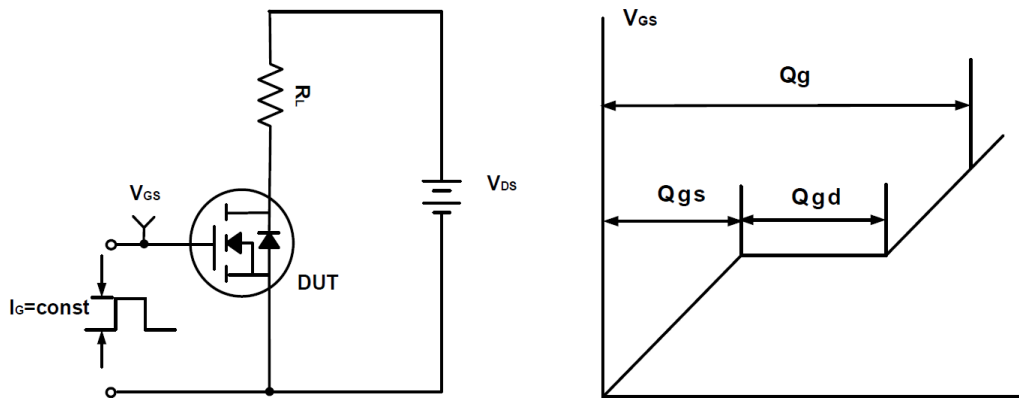


Figure A Gate Charge Test Circuit & Waveforms

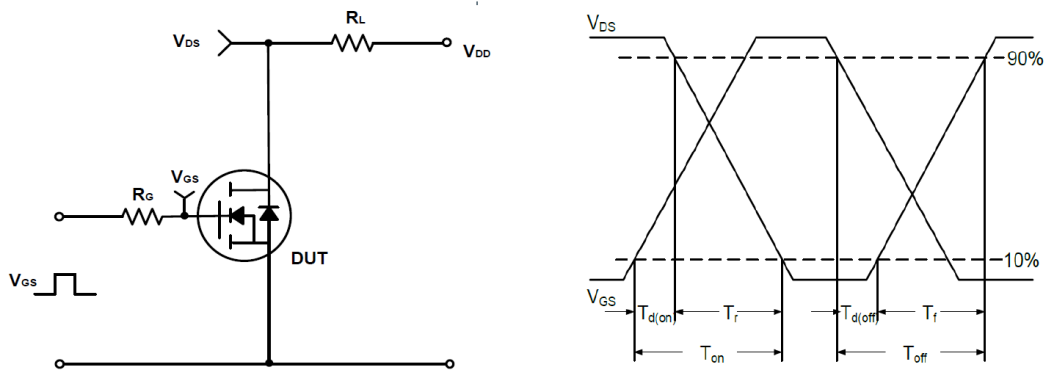


Figure B Switching Test Circuit & Waveforms

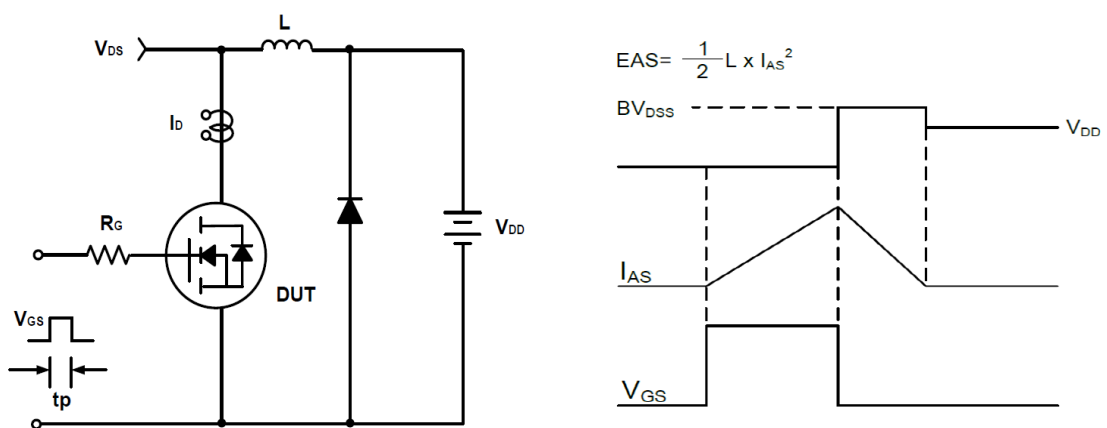
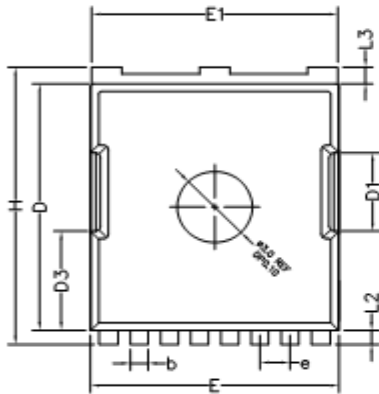


Figure C Unclamped Inductive Switching Circuit & Waveforms

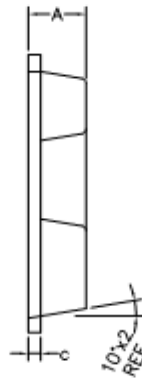


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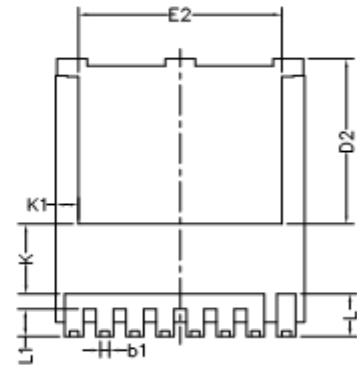
TOLL Package Outline Dimensions (Units: mm)



TOP VIEW



SIDE VIEW



BOTTEM VIEW



SIDE VIEW

COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	2.200	2.300	2.400
b	0.600	0.700	0.900
b1	0.300	—	0.500
c	0.400	0.500	0.600
D	10.280	10.380	10.480
D1	3.200	3.300	3.400
D2	6.850	6.950	7.050
D3	4.18REF		
E	9.800	9.900	10.000
E1	9.700	9.800	9.900
E2	8.000	8.100	8.200
e	1.200BSC		
H	11.480	11.680	11.880
L	1.600	1.800	2.100
L1	1.000	1.150	1.300
L2	0.600 TYPE		
L3	0.600 TYPE		
K	2.900 TYPE		
K1	0.900 TYPE		